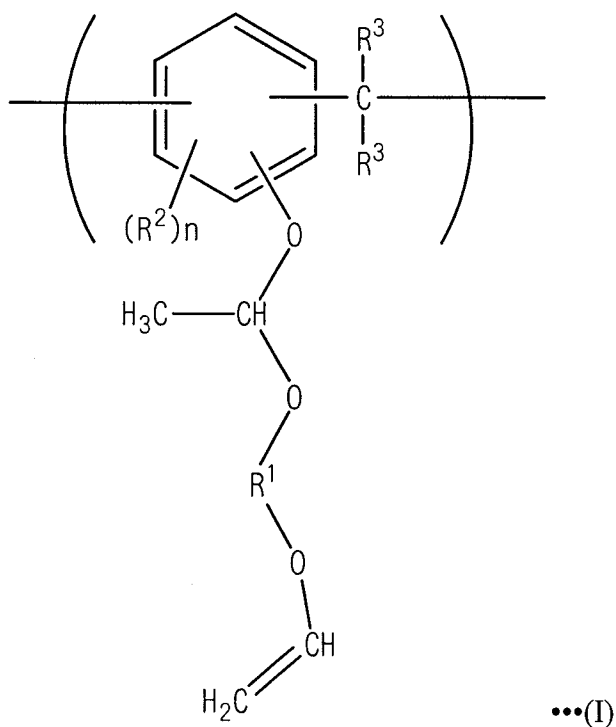


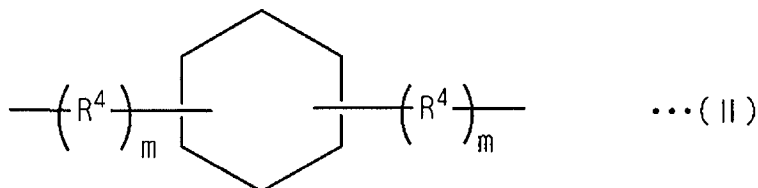
AMENDMENTS TO THE CLAIMS

1. **(Previously presented)** A chemical amplification type positive photoresist composition prepared by dissolving:

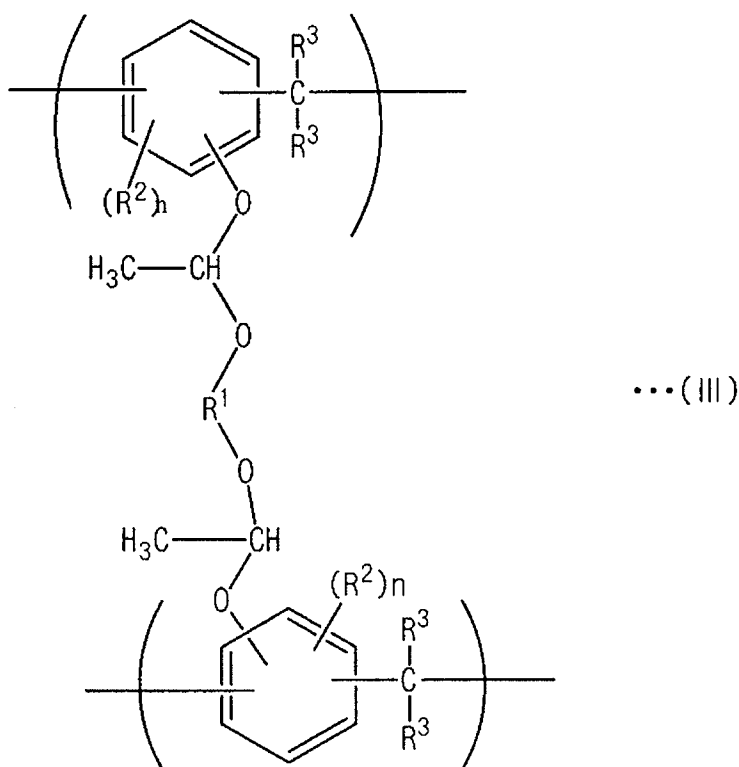
(A) a slightly alkali-soluble or alkali-insoluble novolak resin having a property that solubility in an aqueous alkali solution is enhanced in the presence of an acid, comprising either or both of a constituent unit (a1) represented by the following general formula (I):



wherein R¹ represents either an alkylene group having 1 to 10 carbon atoms which may have a substituent or a group represented by the following general formula (II):



(wherein R^4 represents an alkylene group having 1 to 10 carbon atoms which may have a substituent and m represents 0 or 1), the alkylene group may have an oxygen bond (ether bond) in the main chain, R^2 and R^3 each independently represents a hydrogen atom or an alkyl group having 1 to 3 carbon atoms, and n represents an integer of 1 to 3, and an intermolecular crosslinked moiety (a2) represented by the following general formula (III):



wherein R^1 represents either an alkylene group having 1 to 10 carbon atoms which may have a substituent or a group represented by the above general formula (II) (wherein R^4 represents an alkylene group having 1 to 10 carbon atoms which may have a substituent and m represents 0 or 1), the alkylene group may have an oxygen bond (ether bond) in the main chain, R^2 and R^3 each independently represents hydrogen atom or alkyl group having 1 to 3 carbon atoms, and n represents an integer of 1 to 3; and

(B) a compound generating an acid under irradiation, in an organic solvent, wherein the content of an acid component in the photoresist composition is 10 ppm or less.

2. (Canceled)

3. **(Canceled)**

4. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 1, wherein the component (B) is a compound generating an acid under irradiation with i-rays (365 nm).

5. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 1, which further comprises a basic compound as the component (C).

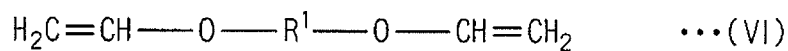
6. **(Original)** The chemical amplification type positive photoresist composition according to claim 5, which comprises the component (C) in the amount of 0.01 to 5 parts by weight based on 100 parts by weight of the resin component contained in the resist composition.

7. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 1, which comprises γ -butyrolactone.

8. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 1, which is used for a thick-film photolithography process used for forming a resist film having a thickness of about 2 to 7 μm .

9. **(Original)** The chemical amplification type positive photoresist composition according to claim 8, wherein the thick-film photolithography process is used for forming a resist pattern for implantation.

10. **(Original)** A method for synthesis of the component (A) of claim 1, which comprises reacting a novolak resin with a crosslinking agent represented by the following general formula (VI):



wherein R^1 represents either an alkylene group having 1 to 10 carbon atoms which may have a substituent or a group represented by the above general formula (II) (wherein R^4 represents an alkylene group having 1 to 10 carbon atoms which may have a substituent and m represents 0 or 1, and the alkylene group may have an oxygen bond (ether bond) in the main chain, in the substantial absence of an acid catalyst.

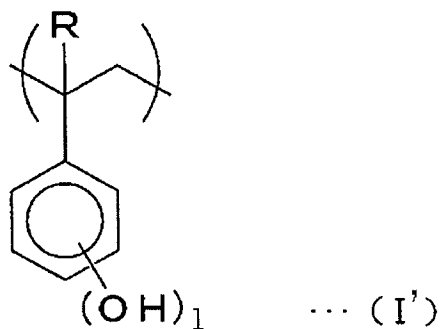
11. **(Canceled)**

12. **(Canceled)**

13. **(Previously presented)** A method for formation of a resist pattern of a thick-film photolithography process, which comprises forming a resist film having a thickness of 2 to 7 μm made of the chemical amplification type positive resist composition of claim 1 on a substrate, and subjecting to selective exposure, post exposure bake (PEB) treatment, and development.

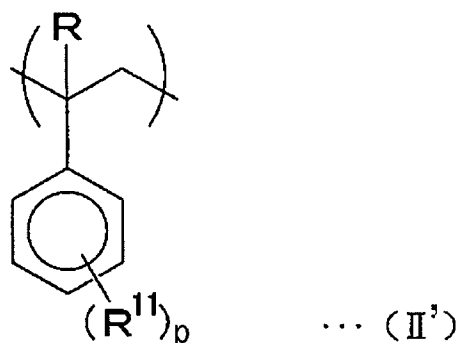
14. **(Original)** The method for formation of a resist pattern according to claim 13, wherein a resist pattern for implantation is formed in the thick-film photolithography process.

15. **(Previously presented)** A chemical amplification type positive photoresist composition comprising (A2) a resin made of a reaction product of (A1) an alkali soluble resin and (C1) a crosslinking polyvinyl ether compound wherein alkali solubility enhances by an action of an acid, and (B1) a photo acid generator generating acid under irradiation with radiation, wherein the component (A1) comprises a unit ($a1'$) derived from (α -methyl)hydroxystyrene represented by the following general formula (I'):



wherein R represents a hydrogen atom or a methyl group and l represents an integer of 1 to 3, and an alkali-insoluble unit (a2') having no acid dissociable dissolution inhibiting group, and wherein a dissolution rate of the component (A1) to an aqueous 2.38% by weight solution of TMAH (tetramethylammonium hydroxide) is from 10 to 100 nm/second, wherein the component (B1) is a poly(bissulfonyl)diazomethane photo acid generator.

16. **(Original)** The chemical amplification type positive photoresist composition according to claim 15, wherein the constituent unit (a2') is a unit derived from (α -methyl)styrene represented by the following general formula (II'):



wherein R represents a hydrogen atom or a methyl group, R¹¹ represents an alkyl group having 1 to 5 carbon atoms and p represents an integer of 0 or 1 to 3.

17. **(Original)** The chemical amplification type positive photoresist composition according to claim 16, wherein the content of constituent unit (a2') in the component (A1) is from 5 to 35 mol%.

18. **(Original)** The chemical amplification type positive photoresist composition according to claim 15, wherein the weight-average molecular weight of the component (A2) is from 20000 to 150000.

19. **(Canceled)**

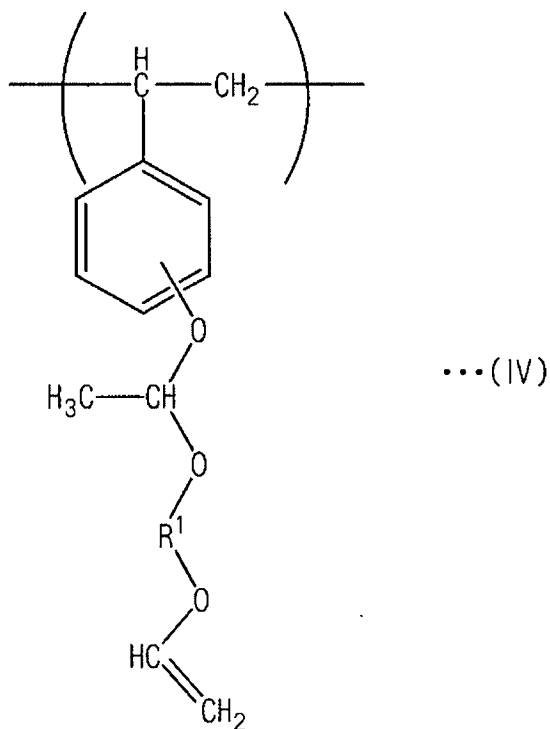
20. **(Canceled)**

21. **(Original)** The chemical amplification type positive photoresist composition according to claim 15, which further comprises a nitrogen-containing organic compound (D').

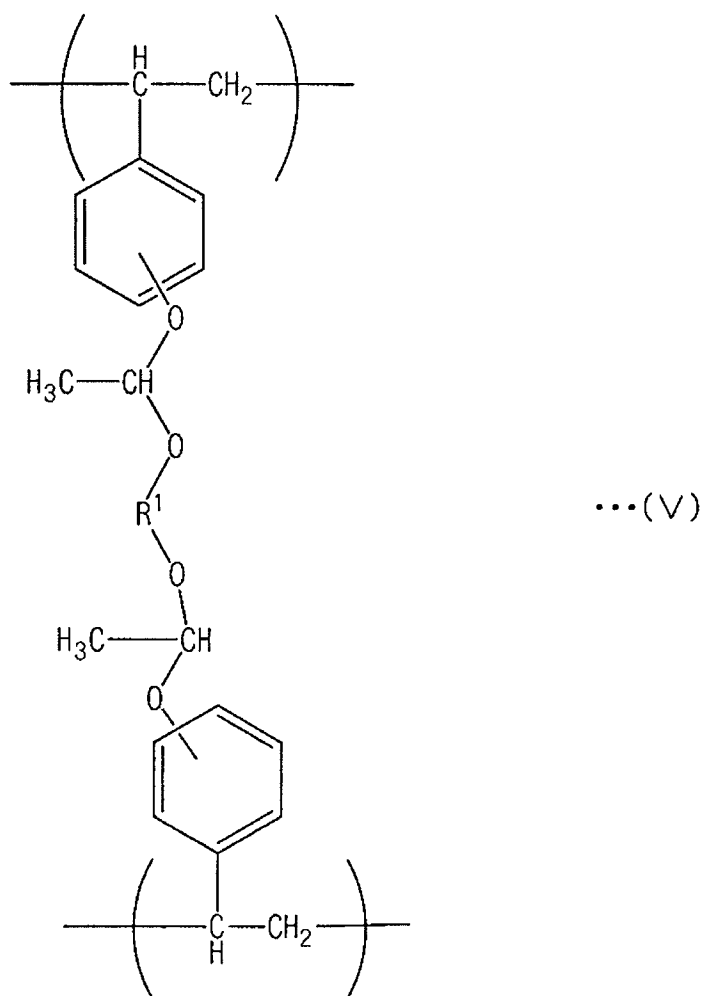
22. **(Original)** A resist pattern forming method, which comprises applying the chemical amplification type positive photoresist composition of claim 15 on a substrate, and subjecting to prebaking, selective exposure, PEB (post exposure bake) and alkali development to form a resist pattern.

23. **(Currently amended)** A chemical amplification type positive photoresist composition prepared by dissolving:

(A') a slightly alkali-soluble or alkali-insoluble polyhydroxystyrenic resin having a property that solubility in an aqueous alkali solution is enhanced in the presence of an acid, comprising either or both or a constituent unit (a'1) represented by the following general formula (IV):



wherein R^1 represents either an alkylene group having 1 to 10 carbon atoms which may have a substituent or a group represented by the above general formula (II) (wherein R^4 represents an alkylene group having 1 to 10 carbon atoms which may have a substituent and m represents 0 or 1), the alkylene group may have a oxygen bond (ether bond) in the main chain, and an intermolecular crosslinked moiety ($a'2$) represented by the following general formula (V):



wherein R^1 represents either an alkylene group having 1 to 10 carbon atoms which may have a substituent or a group represented by the above general formula (II) (wherein R^4 represents an alkylene group having 1 to 10 carbon atoms which may have a substituent and m represents 0 or 1), the alkylene group may have an oxygen bond (ether bond) in the main chain; and

(B) a compound generating an acid under irradiation in an organic solvent,

wherein the content of an acid component in the entire photoresist composition is 10 ppm or less.

24. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 23, wherein the component (B) is a compound generating an acid under irradiation with i-rays (365 nm).

25. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 23, which further comprises a basic compound as the component (C).

26. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 25, which comprises the component (C) in the amount of 0.01 to 5 parts by weight based on 100 parts by weight of the resin component contained in the resist composition.

27. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 23, which comprises γ -butyrolactone.

28. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 23, which is used for a thick-film photolithography process used for forming a resist film having a thickness of about 2 to 7 μm .

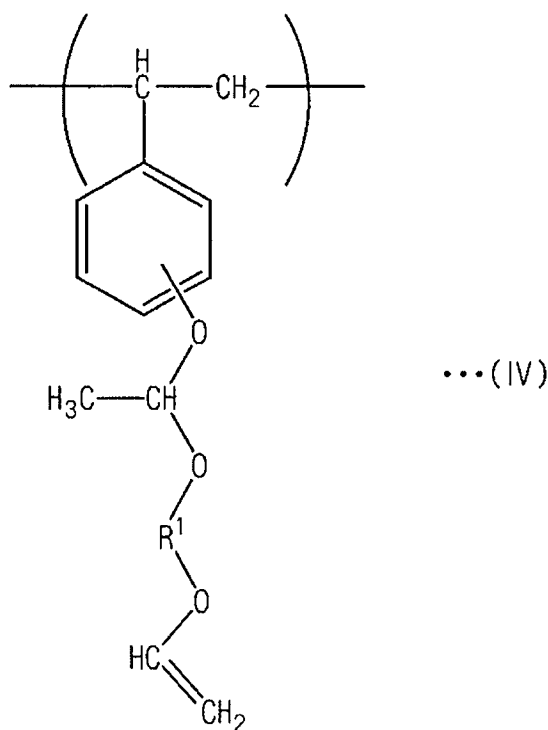
29. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 28, wherein the thick-film photolithography process is used for forming a resist pattern for implantation.

30. **(Previously presented)** A method for formation of a resist pattern of a thick-film photolithography process, which comprises forming a resist film having a thickness of 2 to 7 μm made of the chemical amplification type positive resist composition of claim 23 on a substrate, and subjecting to selective exposure, post exposure bake (PEB) treatment, and development.

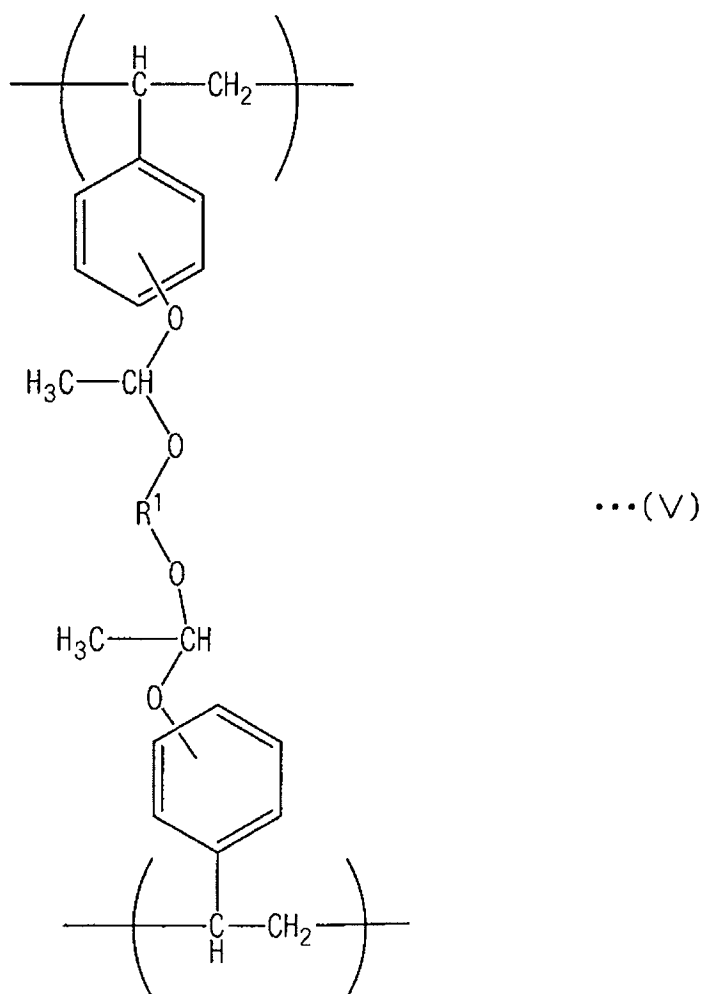
31. **(Currently amended)** The method for formation of a resist pattern according to claim ~~13~~ 30, wherein a resist pattern for implantation is formed in the thick-film photolithography process.

32. **(Currently amended)** A chemical amplification type positive photoresist composition prepared by dissolving:

(A'') a slightly alkali-soluble or alkali-insoluble polyhydroxystyrenic resin having such a property that solubility in an aqueous alkali solution is enhanced in the presence of an acid comprising either or both of a constituent unit (a'1) represented by the following general formula (IV):



wherein R¹ represents either an alkylene group having 1 to 10 carbon atoms which may have a substituent or a group represented by the above general formula (II) (wherein R⁴ represents an alkylene group having 1 to 10 carbon atoms which may have a substituent and m represents 0 or 1), the alkylene group may have an oxygen bond (ether bond) in the main chain, and an intermolecular crosslinked moiety (a'2) represented by the following general formula (V):



wherein R^1 represents either an alkylene group having 1 to 10 carbon atoms which may have a substituent or a group represented by the above general formula (II) (wherein R^4 represents an alkylene group having 1 to 10 carbon atoms which may have a substituent and m represents 0 or 1), the alkylene group may have an oxygen bond (ether bond) in the main chain, and a styrenic constituent unit; and

(B) a compound generating an acid under irradiation in an organic solvent, wherein the content of an acid component in the entire photoresist composition is 10 ppm or less.

33. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 32, wherein the component (B) is a compound generating an acid under irradiation with i-rays (365 nm).

34. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 32, which further comprises a basic compound as the component (C).

35. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 34, which comprises the component (C) in the amount of 0.01 to 5 parts by weight based on 100 parts by weight of the resin component contained in the resist composition.

36. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 32, which comprises γ -butyrolactone.

37. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 32, which is used for a thick-film photolithography process used for forming a resist film having a thickness of about 2 to 7 μm .

38. **(Previously presented)** The chemical amplification type positive photoresist composition according to claim 37, wherein the thick-film photolithography process is used for forming a resist pattern for implantation.

39. **(Previously presented)** A method for formation of a resist pattern of a thick-film photolithography process, which comprises forming a resist film having a thickness of 2 to 7 μm made of the chemical amplification type positive resist composition of claim 32 on a substrate, and subjecting to selective exposure, post exposure bake (PEB) treatment, and development.

40. **(Previously presented)** The method for formation of a resist pattern according to claim 39, wherein a resist pattern for implantation is formed in the thick-film photolithography process.

41. **(New)** The chemical amplification type positive photoresist composition according to claim 23, wherein said organic solvent is a non-ester solvent containing no free acid.

42. **(New)** The chemical amplification type positive photoresist composition according to claim 32, wherein said organic solvent is a non-ester solvent containing no free acid.